

## IN THE CLAIMS

This listing of claims replaces all prior listings.

1. (currently amended) A method for manufacturing a micromachine including an oscillator, comprising:

a step of forming a sacrifice layer around a movable portion of the oscillator, the sacrificial layer comprising silicon dioxide;

a step of covering the sacrifice layer with an overcoat film, followed by the formation of a penetrating hole reaching the sacrifice layer in the overcoat layer;

a step of performing sacrifice-layer etching ~~for removing which removes~~ the sacrifice layer using the penetrating hole in order to form a space around the movable portion; and

a step of performing a film-formation treatment by sputtering at a reduced pressure following the sacrifice-layer etching so as to form a sputtering layer that seals the penetrating hole and is formed in to a wiring layer ~~that seals the penetrating hole,~~

wherein,

the film formation treatment forming a film the sputtering layer is composed of one selected from the group consisting of an aluminum copper film and an aluminum silicon film.

2. (original) The method for manufacturing a micromachine, according to claim 1, wherein the method is applied to a micromachine having means for driving oscillation in the oscillator.

3. (original) The method for manufacturing a micromachine, according to claim 2, wherein static electricity is used as the means for driving oscillation.

4. (original) The method for manufacturing a micromachine, according to claim 2, wherein piezoelectricity is used as the means for driving oscillation.

5. (original) The method for manufacturing a micromachine, according to claim 1, wherein the film-formation treatment at a reduced pressure is a film-formation treatment by sputtering.